

Description

The SX70P03D uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

$V_{DS} = -30V$ $I_D = -70A$

$R_{DS(ON)} < 9.0m\Omega$ @ $V_{GS} = -10V$

Application

Lithium battery protection

Wireless impact

Mobile phone fast charging



Absolute Maximum Ratings (TC=25°C unless otherwise noted)

Symbol	Parameter	Max.	Units
VDSS	Drain-Source Voltage	-30	V
VGSS	Gate-Source Voltage	± 20	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	70	A
$I_D @ T_A = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	50	A
IDM	Pulsed Drain Current ^{note1}	-220	A
EAS	Single Pulsed Avalanche Energy ^{note2}	121	mJ
$P_D @ T_A = 25^\circ C$	Power Dissipation	65.2	W
$R_{\theta JC}$	Thermal Resistance, Junction to Case	2.9	$^\circ C/W$
TJ, TSTG	Operating and Storage Temperature Range	-55 to +175	$^\circ C$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	$V_{GS}=0\text{V}$, $I_D=-250\mu\text{A}$	-30	33	-	V
IDSS	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$	-	-	± 100	nA
VGS(th)	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.0	-1.6	-2.5	V
RDS(on)	Static Drain-Source on-Resistance note3	$V_{GS}=-10\text{V}$, $I_D=-30\text{A}$	-	6.5	9.0	$\text{m}\Omega$
		$V_{GS}=-4.5\text{V}$, $I_D=-20\text{A}$	-	11.6	16	
Ciss	Input Capacitance	$V_{DS}=-15\text{V}$, $V_{GS}=0\text{V}$, $f=1.0\text{MHz}$	-	3564	-	pF
Coss	Output Capacitance		-	416	-	pF
Crss	Reverse Transfer Capacitance		-	373	-	pF
Qg	Total Gate Charge	$V_{DS}=-15\text{V}$, $I_D=-20\text{A}$, $V_{GS}=-10\text{V}$	-	37	-	nC
Qgs	Gate-Source Charge		-	6.5	-	nC
Qgd	Gate-Drain("Miller") Charge		-	9.4	-	nC
td(on)	Turn-on Delay Time	$V_{DD}=-15\text{V}$, $I_D=-30\text{A}$, $V_{GS}=-10\text{V}$, $R_{GEN}=2.5\Omega$	-	16	-	ns
tr	Turn-on Rise Time		-	21	-	ns
td(off)	Turn-off Delay Time		-	68	-	ns
tf	Turn-off Fall Time		-	52	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-55	A
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-220	A
VSD	Drain to Source Diode Forward Voltage	$V_{GS}=0\text{V}$, $I_S=-30\text{A}$	-	-0.8	-1.2	V

Note :

- 1、The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2、The data tested by pulsed , pulse width .The EAS data shows Max. rating .
- 3、The power dissipation is limited by 175°C junction temperature
- 4、EAS condition: $T_J=25^\circ\text{C}$, $V_{DD}=-15\text{V}$, $V_G=-10\text{V}$, $R_G=25\Omega$, $L=0.5\text{mH}$, $I_{AS}=-22\text{A}$
- 5、The data is theoretically the same as ID and IDM , in real applications , should be limited by total power dissipation.

Typical Characteristics

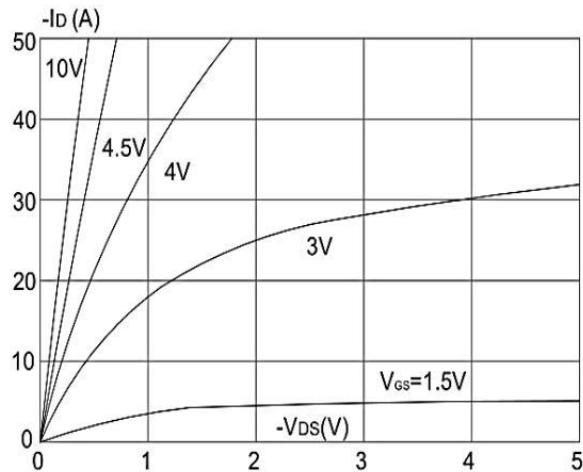


Figure 1: Output Characteristics
R_{DS(ON)} (mΩ)

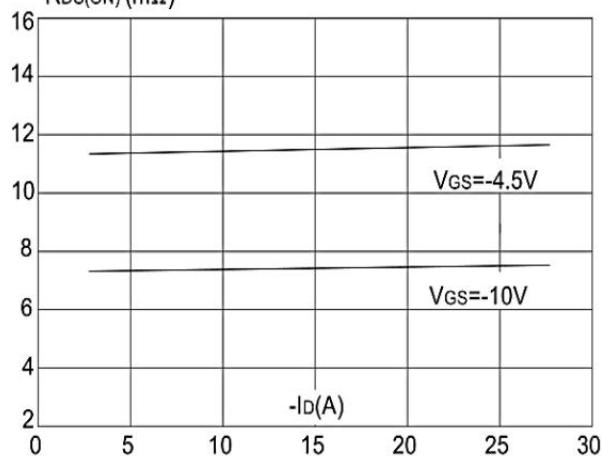


Figure 3: On-resistance vs. Drain Current

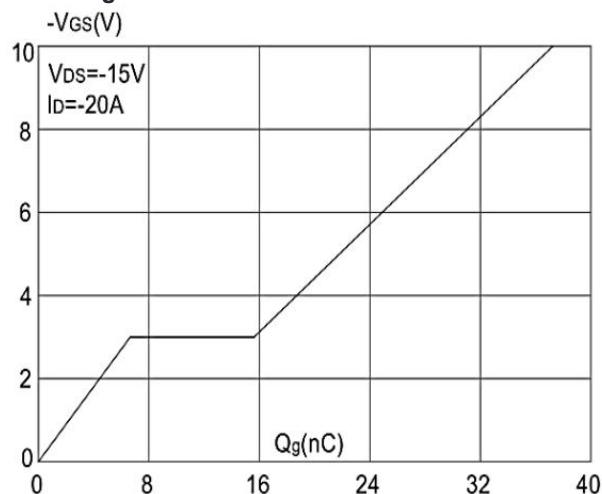


Figure 5: Gate Charge Characteristics

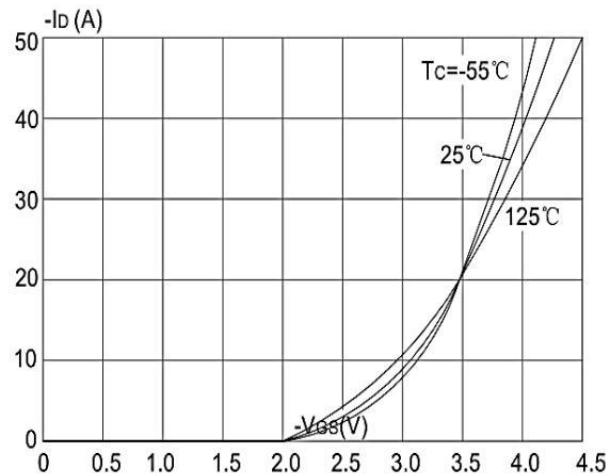


Figure 2: Typical Transfer Characteristics

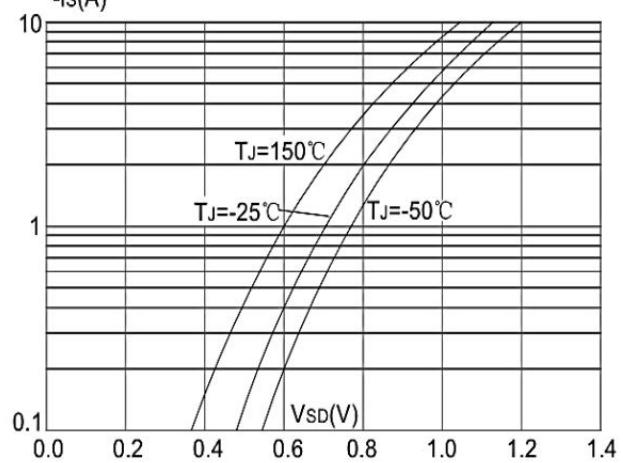


Figure 4: Body Diode Characteristics

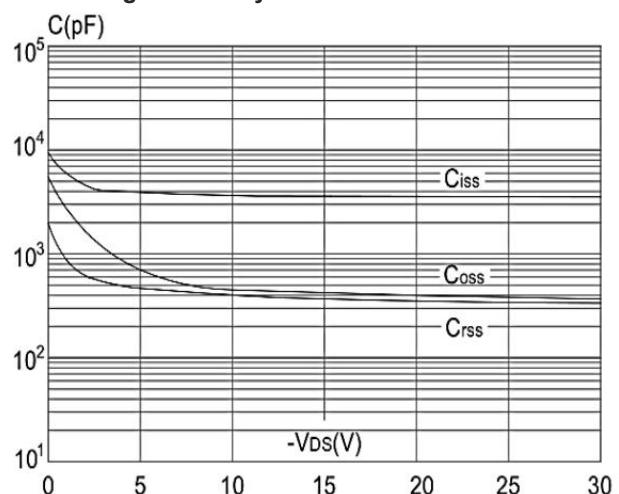
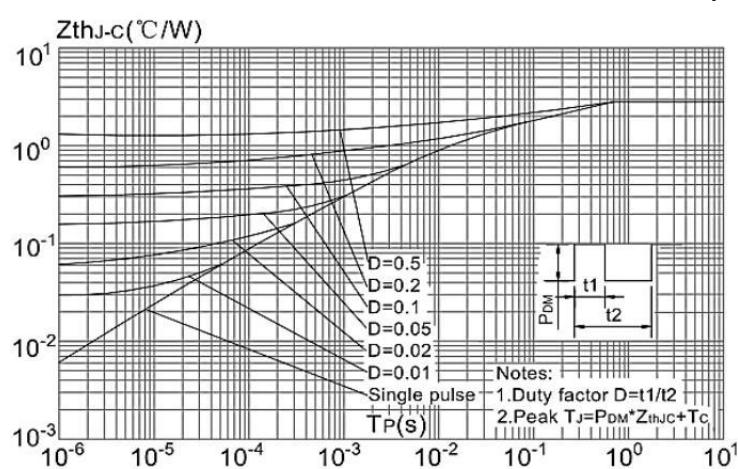
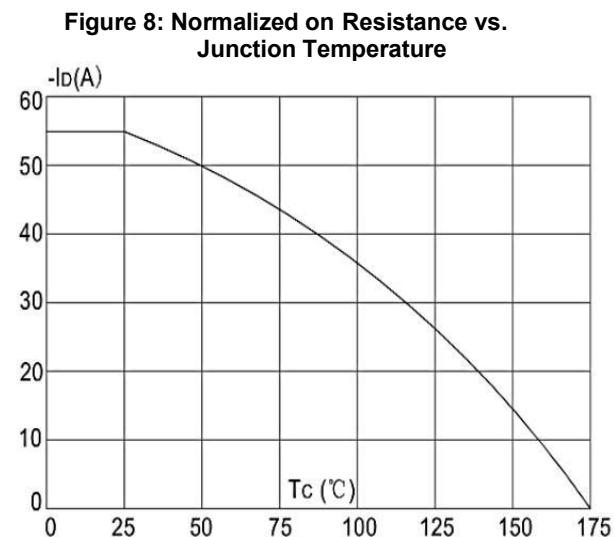
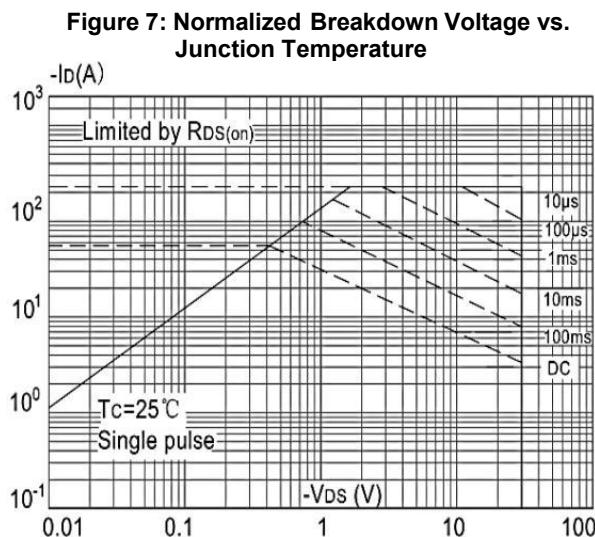
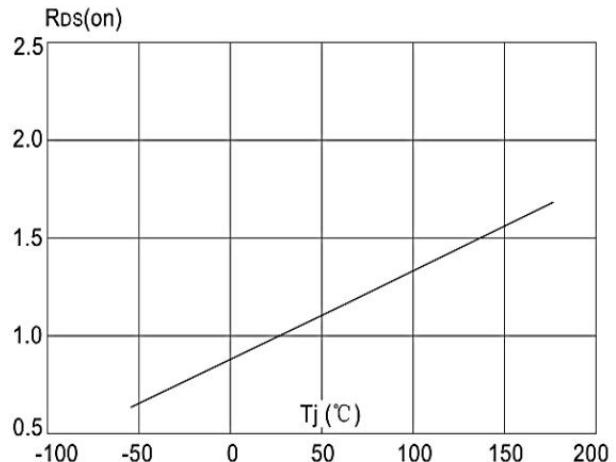
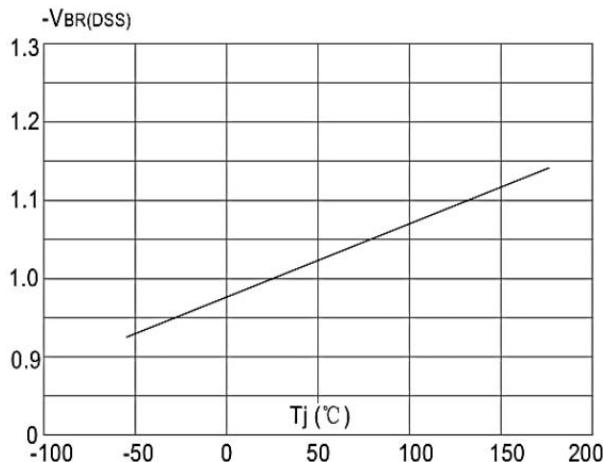
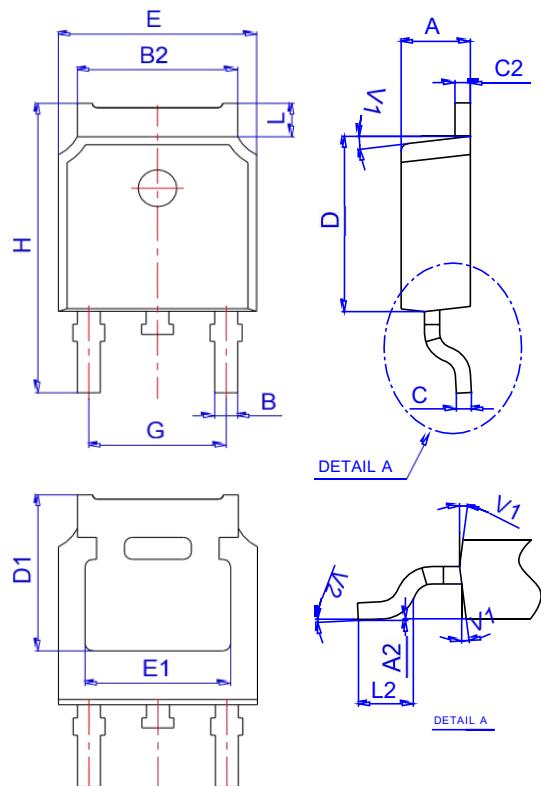


Figure 6: Capacitance Characteristics

Typical Characteristics



Package Mechanical Data:TO-252-3L



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	TO-252-3L		2500